

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC2882

POWER AMPLIFIER APPLICATIONS.

VOLTAGE AMPLIFIER APPLICATIONS.

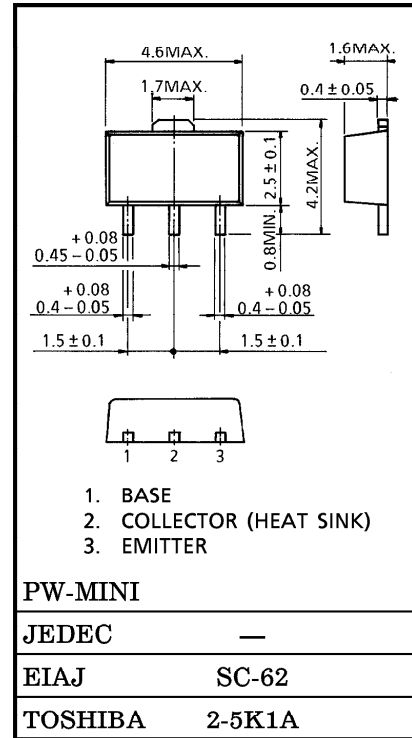
- Suitable for Driver of 30~35 Watts Audio Amplifier
- $P_C=1\sim 2W$  (Mounted Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1202

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB0}$	80	V
Collector-Emitter Voltage	$V_{CE0}$	80	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	400	mA
Base Current	$I_B$	80	mA
Collector Power Dissipation	$P_C$	500	mW
Collector Power Dissipation	$P_C$ (Note)	1000	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

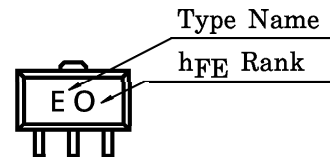
Note : Mounted on ceramic substrate ( $250mm^2 \times 0.8t$ )

Unit in mm



Weight : 0.05g

Marking



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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 80V, I_E = 0$	—	—	0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	—	—	0.1	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 10mA, I_B = 0$	80	—	—	V
DC Current Gain	$h_{FE} (1)$ (Note)	$V_{CE} = 2V, I_C = 50mA$	70	—	240	
	$h_{FE} (2)$	$V_{CE} = 2V, I_C = 200mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE (sat)}$	$I_C = 200mA, I_B = 20mA$	—	—	0.4	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 2V, I_C = 5mA$	—	—	0.8	V
Transition Frequency	$f_T$	$V_{CE} = 10V, I_C = 10mA$	0.55	100	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	10	—	pF

Note :  $h_{FE}$  Classification    O : 70~140,    Y : 120~240

